NIKO-SEM

N-Channel Enhancement Mode Field Effect Transistor

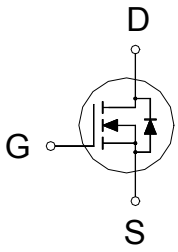
P2806AT

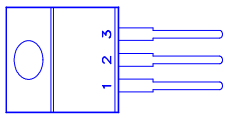
TO-220

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60V	30mΩ	34A





1. GATE
2. DRAIN
3. SOURCE

RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	34	A
	T_C = 100 °C		21	
Pulsed Drain Current[1]		I_{DM}	110	
Avalanche Current		I_{AS}	29	
Avalanche Energy	L = 0.1mH	E_{AS}	41	mJ
Power Dissipation	T_C = 25 °C	P_D	58	W
	T_C = 100 °C		23	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.15	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

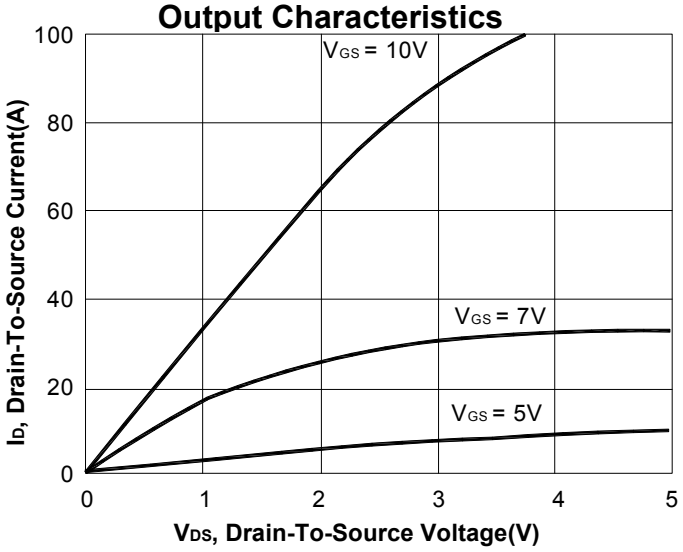
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.8	2.4	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48V, V_{GS} = 0V			1	μA
		V_{DS} = 40V, V_{GS} = 0V, T_J = 125 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	110			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 25A		26	30	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 25A		25		S

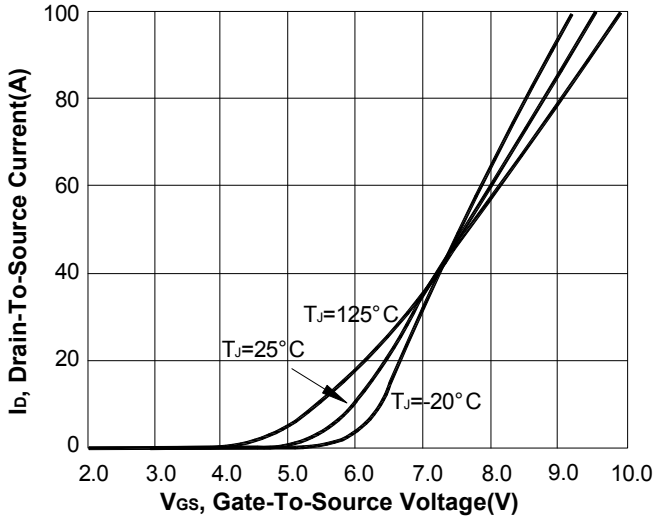
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1240		pF
Output Capacitance	C_{oss}			173		
Reverse Transfer Capacitance	C_{rss}			97		
Gate Resistance	Rg	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.7		Ω
Total Gate Charge[2]	Q_g	V_{DS} =30V, V_{GS} = 10V, I_D = 25A		21		nC
Gate-Source Charge[2]	Q_{gs}			7		
Gate-Drain Charge[2]	Q_{gd}			5		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 0.5$V_{(BR)DSS}$, R_L = 1.5Ω I_D ≅ 20A, V_{GS} = 10V, R_G = 5.6 Ω		10		nS
Rise Time[2]	t_r			145		
Turn-Off Delay Time[2]	$t_{d(off)}$			28		
Fall Time[2]	t_f			77		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				34	A
Forward Voltage[1]	V_{SD}	I_F = 25A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = I_S, dI_F/dt = 100A / μS		40		nS
Reverse Recovery Charge	Q_{rr}			48		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

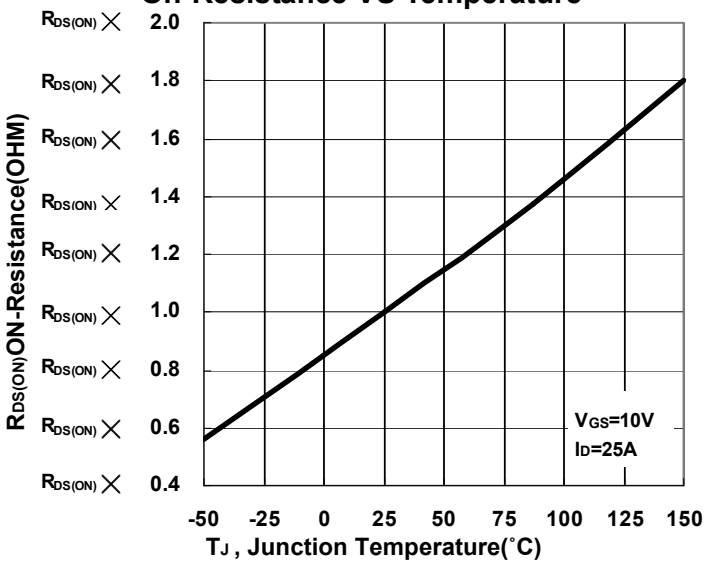
Output Characteristics



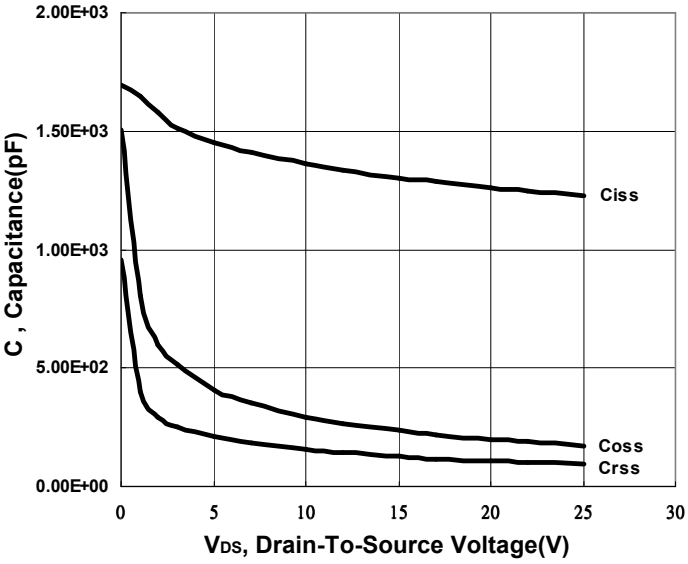
Transfer Characteristics



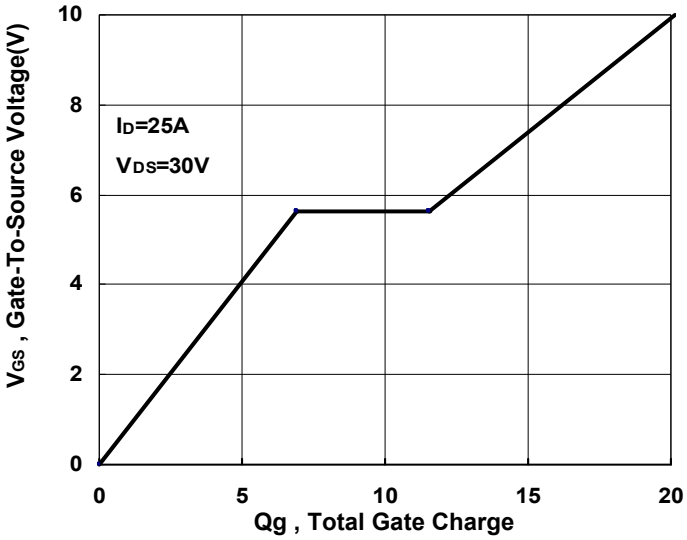
On-Resistance VS Temperature



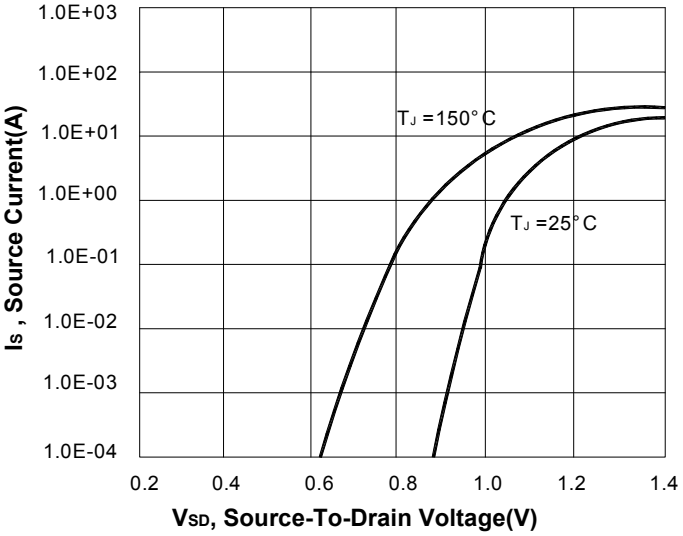
Capacitance Characteristic



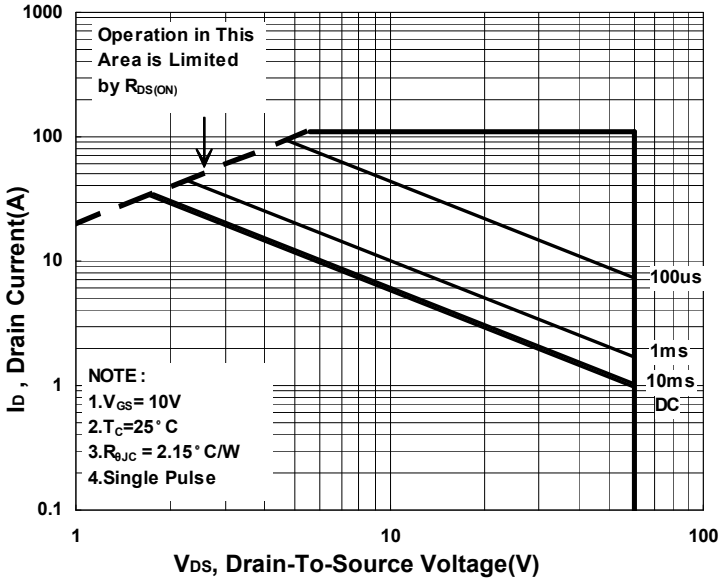
Gate charge Characteristics



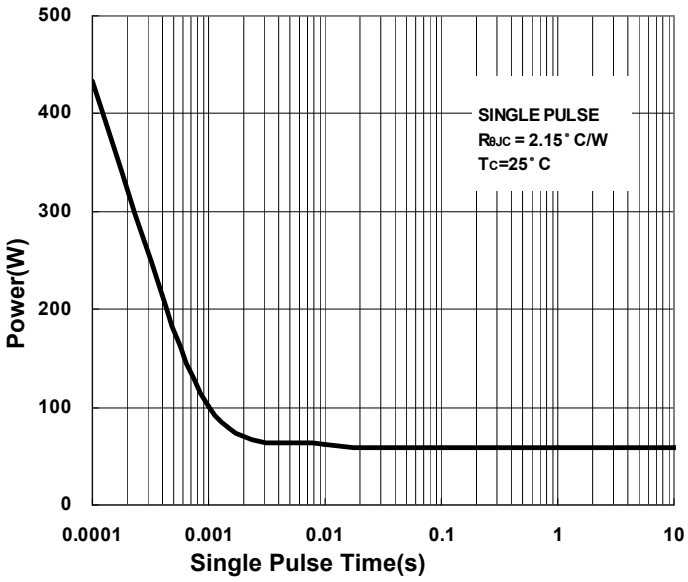
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve